

# Manuel Cardona

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11528383/publications.pdf>

Version: 2024-02-01

196  
papers

20,526  
citations

16411

64  
h-index

11288

136  
g-index

200  
all docs

200  
docs citations

200  
times ranked

10337  
citing authors

#	ARTICLE	IF	CITATIONS
1	Infrared and Raman spectra of the silicon-hydrogen bonds in amorphous silicon prepared by glow discharge and sputtering. <i>Physical Review B</i> , 1977, 16, 3556-3571.	1.1	1,577
2	Fundamentals of Semiconductors. , 1996, , .		1,007
3	Stress-Induced Shifts of First-Order Raman Frequencies of Diamond- and Zinc-Blende-Type Semiconductors. <i>Physical Review B</i> , 1972, 5, 580-593.	1.1	842
4	Piezo-Electroreflectance in Ge, GaAs, and Si. <i>Physical Review</i> , 1968, 172, 816-837.	2.7	835
5	Resonant Raman scattering in ZnO. <i>Physical Review B</i> , 1977, 16, 3753-3761.	1.1	780
6	Electroreflectance at a Semiconductor-Electrolyte Interface. <i>Physical Review</i> , 1967, 154, 696-720.	2.7	761
7	Optical Properties and Band Structure of SrTiO <sub>3</sub> and BaTiO <sub>3</sub> . <i>Physical Review</i> , 1965, 140, A651-A655.	2.7	730
8	Temperature dependence of the first-order Raman scattering by phonons in Si, Ge, and $\alpha$ -Sn: Anharmonic effects. <i>Physical Review B</i> , 1984, 29, 2051-2059.	1.1	714
9	Energy-Band Structure of Germanium and Silicon: The $k$ -p Method. <i>Physical Review</i> , 1966, 142, 530-543.	2.7	598
10	Optical Properties of the Silver and Cuprous Halides. <i>Physical Review</i> , 1963, 129, 69-78.	2.7	578
11	Optical Properties and Band Structure of Wurtzite-Type Crystals and Rutile. <i>Physical Review</i> , 1965, 137, A1467-A1476.	2.7	523
12	Acoustic deformation potentials and heterostructure band offsets in semiconductors. <i>Physical Review B</i> , 1987, 35, 6182-6194.	1.1	522
13	Band parameters of semiconductors with zincblende, wurtzite, and germanium structure. <i>Journal of Physics and Chemistry of Solids</i> , 1963, 24, 1543-1555.	1.9	434
14	Optical Properties and Band Structure of Group IV-VI and Group V Materials. <i>Physical Review</i> , 1964, 133, A1685-A1697.	2.7	397
15	Isotope effects on the optical spectra of semiconductors. <i>Reviews of Modern Physics</i> , 2005, 77, 1173-1224.	16.4	380
16	Dependence of the direct energy gap of GaAs on hydrostatic pressure. <i>Physical Review B</i> , 1975, 12, 5729-5738.	1.1	302
17	Fundamental Reflectivity and Band Structure of ZnTe, CdTe, and HgTe. <i>Physical Review</i> , 1963, 131, 98-103.	2.7	273
18	Thermoreflectance in Semiconductors. <i>Physical Review</i> , 1968, 176, 950-960.	2.7	265

#	ARTICLE	IF	CITATIONS
19	Densities of valence states of amorphous and crystalline III-V and II-VI semiconductors. Physical Review B, 1974, 9, 2627-2648.	1.1	234
20	Effects of Uniaxial Stress on the Indirect Exciton Spectrum of Silicon. Physical Review B, 1971, 3, 2623-2636.	1.1	228
21	Effect of Carrier Concentration on the Raman Frequencies of Si and Ge. Physical Review B, 1972, 5, 1440-1454.	1.1	211
22	Raman scattering in pure and hydrogenated amorphous germanium and silicon. Journal of Non-Crystalline Solids, 1979, 32, 405-419.	1.5	200
23	Electron Effective Masses of InAs and GaAs as a Function of Temperature and Doping. Physical Review, 1961, 121, 752-758.	2.7	197
24	Pressure dependence of Raman phonons of Ge and 3C-SiC. Physical Review B, 1982, 25, 1151-1160.	1.1	183
25	Modulated Piezoreflectance in Semiconductors. Physical Review B, 1970, 1, 672-682.	1.1	174
26	Fundamental Reflectivity Spectrum of Semiconductors with Zinc-Blende Structure. Journal of Applied Physics, 1961, 32, 2151-2155.	1.1	173
27	Electroreflectance in the GaAs-GaP Alloys. Physical Review, 1966, 146, 601-610.	2.7	169
28	Absorption Spectrum of Germanium and Zinc-Blende-Type Materials at Energies Higher than the Fundamental Absorption Edge. Journal of Applied Physics, 1963, 34, 813-818.	1.1	168
29	Photoluminescence in heavily doped GaAs. I. Temperature and hole-concentration dependence. Physical Review B, 1980, 22, 886-893.	1.1	164
30	Interference effects: A key to understanding forbidden Raman scattering by LO phonons in GaAs. Physical Review B, 1985, 31, 3696-3704.	1.1	162
31	Intrinsic Piezobirefringence of Ge, Si, and GaAs. Physical Review, 1969, 184, 821-829.	2.7	158
32	First- and second-order Raman spectra of galena (PbS). Journal of Applied Physics, 2002, 92, 4375-4380.	1.1	144
33	Electron-phonon interaction in tetrahedral semiconductors. Solid State Communications, 2005, 133, 3-18.	0.9	140
34	Bond Charge, Bond Polarizability, and Phonon Spectra in Semiconductors. Physical Review Letters, 1975, 34, 580-583.	2.9	138
35	Ultraviolet Reflection Spectrum of Cubic CdS. Physical Review, 1965, 140, A633-A637.	2.7	136
36	Light scattering by free carrier excitations in semiconductors. Topics in Applied Physics, 1984, , 5-150.	0.4	135

#	ARTICLE	IF	CITATIONS
37	Raman spectroscopy of vibrations in superlattices. , 1989, , 49-152.		132
38	Angle-resolved uv photoemission and electronic band structures of the lead chalcogenides. Physical Review B, 1978, 18, 3847-3871.	1.1	130
39	Microscopic theory of intervalley scattering in GaAs: k dependence of deformation potentials and scattering rates. Journal of Applied Physics, 1990, 68, 1682-1693.	1.1	126
40	Resonant First- and Second-Order Raman Scattering in GaP. Physical Review B, 1973, 8, 2795-2809.	1.1	117
41	Temperature Coefficient of the Refractive Index of Diamond- and Zinc-Blende-Type Semiconductors. Physical Review B, 1970, 2, 3193-3197.	1.1	114
42	Second-Order Raman Spectrum of Germanium. Physical Review B, 1973, 7, 2545-2551.	1.1	113
43	Isotope and temperature shifts of direct and indirect band gaps in diamond-type semiconductors. Physical Review B, 1992, 45, 3376-3385.	1.1	108
44	Electroreflectance at a Semiconductor-Electrolyte Interface. Physical Review Letters, 1965, 15, 883-885.	2.9	106
45	Reflectivity of Gray Tin Single Crystals in the Fundamental Absorption Region. Physical Review, 1962, 125, 1291-1296.	2.7	99
46	Infrared Dielectric Constant and Ultraviolet Optical Properties of Solids with Diamond, Zinc Blende, Wurtzite, and Rocksalt Structure. Journal of Applied Physics, 1965, 36, 2181-2186.	1.1	95
47	Resonant Raman scattering in germanium. Solid State Communications, 1972, 10, 591-595.	0.9	93
48	Isotopic effects on the lattice constant in compound semiconductors by perturbation theory: Anab initio calculation. Physical Review B, 1996, 54, 11305-11310.	1.1	93
49	Temperature dependence of the optical phonons and transverse effective charge in 3C-SiC. Physical Review B, 1982, 25, 3889-3896.	1.1	92
50	Dependence of the indirect energy gap of silicon on hydrostatic pressure. Solid State Communications, 1975, 17, 1021-1024.	0.9	91
51	Self-energy effects of the optical phonons of heavily doped $\text{p}^+\text{GaAs}$ and $\text{p}^+\text{Ge}$ . Physical Review B, 1981, 23, 6592-6602.	1.1	90
52	Effect of Temperature and Doping on the Reflectivity of Germanium in the Fundamental Absorption Region. Physical Review, 1961, 122, 1382-1388.	2.7	86
53	Infrared absorption in hydrogenated amorphous and crystallized germanium. Journal of Non-Crystalline Solids, 1979, 32, 421-430.	1.5	86
54	Intervalley deformation potentials and scattering rates in zinc blende semiconductors. Applied Physics Letters, 1989, 54, 614-616.	1.5	84

#	ARTICLE	IF	CITATIONS
55	Photoluminescence in heavily doped GaAs. II. Hydrostatic pressure dependence. Physical Review B, 1980, 22, 894-903.	1.1	83
56	New Evidence for the Existence of Exciton Effects at Hyperbolic Critical Points. Physical Review, 1968, 174, 828-830.	2.7	81
57	Interaction between electronic and vibronic Raman scattering in heavily doped silicon. Solid State Communications, 1973, 13, 325-328.	0.9	79
58	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. Physical Review B, 1993, 48, 7915-7929.	1.1	79
59	Temperature dependence of the dielectric function and the interband critical-point parameters of GaSb. Physical Review B, 1991, 43, 4349-4360.	1.1	77
60	Energy-Band Structure and Optical Spectrum of Grey Tin. Physical Review B, 1970, 2, 352-363.	1.1	76
61	Temperature Dependence of the Energy Gap of Semiconductors in the Low-Temperature Limit. Physical Review Letters, 2004, 92, 196403.	2.9	75
62	The dielectric function of AlSb from 1.4 to 5.8 eV determined by spectroscopic ellipsometry. Journal of Applied Physics, 1989, 66, 383-387.	1.1	74
63	Effects of isotopic composition on the lattice dynamics of CuCl. Physical Review B, 1997, 56, 210-220.	1.1	73
64	Excitons at the Absorption Edge in Zinc Blende-Type Semiconductors. Physical Review Letters, 1962, 8, 90-91.	2.9	70
65	Resonance Raman scattering by LO phonons in $\text{Cd}_{1-x}\text{Hg}_x\text{Te}$ at the $E_0 + \hat{\Gamma}$ gap. Physical Review B, 1985, 31, 3705-3711.	1.1	69
66	Electroreflectance Measurements on $\text{Mg}_2\text{Si}$ , $\text{Mg}_2\text{Ge}$ , and $\text{Mg}_2\text{Sn}$ . Physical Review, 1968, 176, 905-908.	2.7	66
67	Spatial dispersion in the dielectric constant of GaAs. Solid State Communications, 1971, 9, 1421-1424.	0.9	66
68	Evidence for Normal Regions at Low Temperatures in the Superconducting Mixed State. Physical Review Letters, 1964, 12, 657-659.	2.9	65
69	Resonant Raman scattering and interference effects of LO phonons at the $E_0 + \hat{\Gamma}$ gap of InP. Physical Review B, 1986, 33, 5473-5481.	1.1	65
70	Isotopic Mass and Lattice Constant: X-ray Standing Wave Measurements. , 1998, 282, 930-932.		64
71	Effect of hydrostatic pressure on the direct absorption edge of germanium. Physical Review B, 1977, 15, 875-879.	1.1	63
72	Valence band symmetry and deformation potentials of ZnO. Solid State Communications, 1968, 6, 239-242.	0.9	61

#	ARTICLE	IF	CITATIONS
73	Intraband Raman scattering by free carriers in heavily doped $n^{\sim}$ Si. Physical Review B, 1977, 16, 3579-3595.	1.1	59
74	Optical Properties of Some Compound Semiconductors in the 36-150-eV Region. Physical Review B, 1970, 1, 2605-2612.	1.1	56
75	Interference between Allowed and Forbidden Raman Scattering by Longitudinal-Optical Phonons in GaAs. Physical Review Letters, 1983, 51, 1297-1299.	2.9	56
76	Valence Band Structure of PbS from Angle-Resolved Photoemission. Physical Review Letters, 1977, 38, 1033-1036.	2.9	55
77	Electroreflectance and Spin-Orbit Splitting in III-V Semiconductors. Physical Review Letters, 1966, 16, 48-50.	2.9	54
78	Transverse electroreflectance in semi-insulating silicon and gallium arsenide. Journal of Physics and Chemistry of Solids, 1970, 31, 227-246.	1.9	54
79	Optical Studies of the Band Structure of InP. Journal of Applied Physics, 1961, 32, 958-958.	1.1	53
80	Light scattering as a form of modulation spectroscopy. Surface Science, 1973, 37, 100-119.	0.8	52
81	Reflectivity of Semiconductors with Wurtzite Structure. Physical Review, 1963, 129, 1068-1069.	2.7	51
82	Raman scattering in high Tc superconductors: phonons, electrons, and electron-phonon interaction. Physica C: Superconductivity and Its Applications, 1999, 317-318, 30-54.	0.6	51
83	Stress-Induced Exchange Splitting of Hyperbolic Excitons in GaAs. Physical Review Letters, 1969, 22, 933-936.	2.9	50
84	Dependence of the direct energy gap of GaP on hydrostatic pressure. Solid State Communications, 1985, 55, 327-331.	0.9	49
85	The temperature dependence of the band gaps in InP, InAs, InSb, and GaSb. Solid State Communications, 1991, 77, 485-488.	0.9	49
86	Piezoelectroreflectance in GaAs. Physical Review Letters, 1966, 16, 942-944.	2.9	48
87	Strain dependence of effective masses in tetrahedral semiconductors. Physical Review B, 1978, 17, 726-740.	1.1	48
88	Effect of isotope substitution and doping on the Raman spectrum of galena (PbS). Solid State Communications, 2005, 134, 565-570.	0.9	48
89	Piezobirefringence and Deformation Potentials of the Alkali Halides. Physical Review, 1969, 177, 1351-1357.	2.7	47
90	Resonant spin-flip Raman scattering on donor and acceptor states in ZnTe. Physical Review B, 1981, 23, 4129-4139.	1.1	47

#	ARTICLE	IF	CITATIONS
91	Deformation Potentials of the Indirect and Direct Absorption Edges of AlSb. Physical Review B, 1970, 1, 1436-1442.	1.1	46
92	Raman scattering by electronic excitations in semiconductors and in high T <sub>c</sub> superconductors. Journal of Low Temperature Physics, 1995, 99, 205-221.	0.6	46
93	Valence bands of the Mg <sub>2</sub> X (X=Si, Ge, Sn) semiconducting compounds. Physical Review B, 1976, 14, 2559-2568.	1.1	44
94	Piezoresistance and the conduction-band minima of GaAs. Physical Review B, 1978, 17, 741-751.	1.1	42
95	Phonons, Strains, and Pressure in Semiconductors. Semiconductors and Semimetals, 1998, 55, 117-233.	0.4	41
96	Electroreflectance and band structure of gray tin. Solid State Communications, 1966, 4, 319-321.	0.9	40
97	Infrared absorption in amorphous silicon from ab initio molecular dynamics. Applied Physics Letters, 1997, 71, 2692-2694.	1.5	40
98	Polarization effects in the ultraviolet reflection of crystals with wurtzite structure. Solid State Communications, 1963, 1, 109-115.	0.9	39
99	Two-phonon Raman spectra of Si and GaP. Solid State Communications, 1972, 10, 961-965.	0.9	39
100	Correlation between the Josephson coupling energy and the condensation energy in bilayer cuprate superconductors. Physical Review B, 2001, 64, .	1.1	38
101	Electroreflectance in AlSb: Observation of the Direct Band Edge. Physical Review Letters, 1966, 16, 644-646.	2.9	37
102	Resonant Raman scattering in the II-IV semiconductors Mg <sub>2</sub> Si, Mg <sub>2</sub> Ge, and Mg <sub>2</sub> Sn. Physical Review B, 1976, 14, 3520-3531.	1.1	36
103	Energy band structure of germanium and gallium arsenide: The $\Gamma$ method. Journal of Physics and Chemistry of Solids, 1966, 27, 423-425.	1.9	34
104	X <sub>1</sub> and X <sub>3</sub> states of electrons and phonons in zincblende type semiconductors. Solid State Communications, 1988, 67, 927-930.	0.9	33
105	Photorefectance and electroreflectance in silicon. Solid State Communications, 1969, 7, 879-882.	0.9	32
106	Effects of Free Carriers on Zone-Center Vibrational Modes in Heavily Doped p-type Si. I. Acoustical Modes. Physical Review B, 1973, 8, 4723-4733.	1.1	32
107	Resonant Raman scattering by plasmons and LO phonons near the $E_1$ and $E_1 + \hbar\omega_p$ gaps of GaSb. Physical Review B, 1987, 36, 7469-7485.	1.1	32
108	Electron-phonon interaction at the direct gap of the copper halides. Solid State Communications, 1996, 98, 27-30.	0.9	32

#	ARTICLE	IF	CITATIONS
109	Transverse reduced mass of the $E_1$ and $E_1 + \hbar\omega_1$ transitions in silicon. <i>Physical Review B</i> , 1977, 15, 5999-6000.	1.1	31
110	Optical investigation of the band structure of GaSb. <i>European Physical Journal A</i> , 1961, 161, 99-102.	1.0	30
111	X-ray and far ultraviolet photoemission of AlSb. <i>Solid State Communications</i> , 1972, 11, 1619-1623.	0.9	30
112	Comment on "Raman Spectroscopy of excited states in $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ -InP single quantum wells grown by chemical-beam epitaxy". <i>Physical Review B</i> , 1988, 37, 1011-1012.	1.1	30
113	Effect of heavy doping on the optical properties and band structure of GaAs. <i>Physical Review B</i> , 1993, 47, 7071-7079.	1.1	30
114	Resonances of a Small Plasma Sphere in a Magnetic Field. <i>Physical Review</i> , 1963, 129, 991-997.	2.7	29
115	Raman scattering by two LO-phonons near $\Gamma$ in GaAs. <i>Solid State Communications</i> , 1981, 39, 1071-1075.	0.9	28
116	Path-integral molecular dynamics simulation of $\langle \mathbf{C}^2 \rangle$ . <i>Physical Review B</i> , 2008, 77, .	1.1	28
117	Electronic surface states in germanium and silicon. <i>Solid State Communications</i> , 1966, 4, 271-274.	0.9	27
118	Vibrational spectra of $\alpha$ -Si, $\beta$ -Si, $\alpha$ -Ge, $\beta$ -Ge: Bethe-lattice calculations. <i>Physical Review B</i> , 1983, 28, 880-888.	1.1	27
119	Raman scattering in high- $T_c$ superconductors. <i>Physica C: Superconductivity and Its Applications</i> , 1991, 185-189, 65-71.	0.6	27
120	Optical constants of germanium and gray tin the $\epsilon$ method. <i>Solid State Communications</i> , 1967, 5, 513-516.	0.9	26
121	Modulation Spectroscopy of Semiconductors. , 1970, , 125-173.		26
122	Microwave Surface Impedance of Superconductors of the Second Kind: In-Bi Alloys. <i>Physical Review Letters</i> , 1964, 12, 101-103.	2.9	25
123	Band structure of gray tin under uniaxial stress. <i>Solid State Communications</i> , 1967, 5, 233-235.	0.9	24
124	Effect of free carriers on the elastic constants of p-type silicon and germanium. <i>Physical Review B</i> , 1976, 13, 5429-5441.	1.1	24
125	First principles calculation of the real part of phonon self energy in compound semiconductors. <i>Physica B: Condensed Matter</i> , 1999, 263-264, 687-690.	1.3	24
126	Optical Constants of Insulators: Dispersion Relations. , 1969, , 137-151.		24



#	ARTICLE	IF	CITATIONS
127	Effective intervalley deformation potentials in the description of time-resolved and hot-electron luminescence. Solid State Communications, 1990, 76, 877-879.	0.9	23
128	Derivative spectrum of indirect excitons in AlSb. Solid State Communications, 1969, 7, 441-444.	0.9	22
129	Electronic properties of clean and oxygen covered (100) cleaved surfaces of PbS. Surface Science, 1980, 92, 385-392.	0.8	22
130	Are transverse phonons important for $\hat{\Gamma}^c$ - X-intervalley scattering?. Solid-State Electronics, 1989, 32, 1585-1589.	0.8	22
131	Resonant Raman scattering by LO phonons near the $E_0 + \hat{\Gamma}^c$ gap of GaSb. Physical Review B, 1987, 35, 9619-9624.	1.1	21
132	Light scattering by plasmons in germanium. Physical Review B, 1984, 29, 3737-3739.	1.1	20
133	Electronic Raman scattering in heavily doped p-type germanium. Physical Review B, 1985, 32, 8071-8077.	1.1	19
134	Ultrafast initial relaxation of hot electrons and holes in tetrahedral semiconductors via deformation potential interaction: Theory and experiment. Applied Physics Letters, 1990, 57, 2838-2840.	1.5	19
135	Photoemission of GaAs and InSb core levels. Solid State Communications, 1972, 11, 1655-1658.	0.9	18
136	Microscopic theory of intervalley scattering in InP. Physical Review B, 1991, 44, 13446-13451.	1.1	18
137	Intra- and inter-valence-band electronic Raman scattering in heavily doped p-GaAs. Physical Review B, 1980, 22, 1905-1911.	1.1	17
138	Vibrations in amorphous silicon and its alloys. Journal of Molecular Structure, 1986, 141, 93-107.	1.8	17
139	Full-zone analysis of relativistic spin splitting at band anticrossings: The case of zinc-blende semiconductors. Physical Review B, 2010, 81, .	1.1	17
140	Resonant Raman scattering in germanium and zincblende-type semiconductors temperature dependence. Solid State Communications, 1971, 9, 1235-1238.	0.9	16
141	The citation impact outside references $\hat{\Gamma}^c$ formal versus informal citations. Scientometrics, 2009, 80, 1-21.	1.6	16
142	Temperature Dependence of the Band Structure of Semiconductors: Electron-Phonon Interaction. Physics and Chemistry of Materials With Low-dimensional Structures, 1989, , 51-64.	1.0	16
143	Intrinsic piezobirefringence of AlSb. Solid State Communications, 1969, 7, 1113-1117.	0.9	15
144	Comment on $\hat{\Gamma}^c$ g-factor anisotropy of conduction electrons in InSb $\hat{\Gamma}^c$ . Physical Review B, 1986, 34, 7402-7403.	1.1	15

#	ARTICLE	IF	CITATIONS
145	Spin relaxation of holes in the split-hole band of InP and GaSb. Physical Review B, 1987, 35, 3843-3853.	1.1	14
146	Temperature dependence of the dielectric function and the interband critical-point parameters of GaP. Thin Solid Films, 1993, 233, 185-188.	0.8	14
147	Self-consistent calculation of intervalley deformation potentials in GaAs and Ge. Journal of Applied Physics, 1993, 74, 2117-2119.	1.1	14
148	Dependence of the excitation energies of boron in diamond on isotopic mass. Solid State Communications, 2001, 121, 7-8.	0.9	14
149	Chapter 5 Optical Absorption above the Fundamental Edge. Semiconductors and Semimetals, 1967, 3, 125-151.	0.4	13
150	Thermoreflectance in the alkali metals. Solid State Communications, 1968, 6, 313-316.	0.9	13
151	Variation of the Ratio $\rho_{33}/\rho_{11}$ in the Immediate Vicinity of $T_c$ . Physical Review, 1969, 187, 766-767.	2.7	13
152	Conduction band minima of InP: Ordering and absolute energies. Applied Physics Letters, 1990, 57, 2339-2341.	1.5	13
153	Resonant Raman Scattering by Spin-Density Fluctuations in n-type Germanium. Physical Review Letters, 1985, 55, 1132-1135.	2.9	12
154	Temperature effects on valence bands in semiconducting lead chalcogenides. Solid State Communications, 1979, 32, 353-356.	0.9	11
155	A new application of the diamond anvil cell: Measurements under uniaxial stress. Solid State Communications, 1981, 38, 1109-1112.	0.9	11
156	Luminescence above the gap in heavily Zn-doped GaAs. Solid State Communications, 1979, 32, 1027-1030.	0.9	10
157	Ellipsometric investigations of piezo-optical effects. Thin Solid Films, 1998, 313-314, 10-17.	0.8	10
158	Phonons in isotopically modified semiconductors and high $T_c$ superconductors. Physica B: Condensed Matter, 1999, 263-264, 376-380.	1.3	10
159	Isotope effects on the lattice parameter of cubic SiC. Physical Review B, 2009, 79, .	1.1	10
160	Modulation spectroscopy of semiconductors. , 1970, , 125-173.		8
161	Anomalous Behavior of $\rho_{33}/\rho_{11}$ near $T_c$ for Sn-In and In-Bi Alloy Systems. Physical Review B, 1970, 2, 2512-2519.	1.1	7
162	Elastic constants and Raman frequencies of heavily doped Si under uniaxial stress. Solid State Communications, 1973, 12, 553-556.	0.9	7

#	ARTICLE	IF	CITATIONS
163	Intervalley scattering times from the rigid-pseudoion method. , 1990, 1282, 78.		7
164	Optical Properties I. , 1996, , 233-331.		6
165	Optical Properties I. , 1999, , 233-331.		6
166	Resonant Raman Scattering in Semiconductors. Physica Scripta, 1989, T25, 201-205.	1.2	6
167	Electron-phonon interaction and phonon softening in ferro-electrics and semiconductors. Ferroelectrics, 1984, 53, 49-58.	0.3	5
168	The disaster of the Nazi-power in science as reflected by some leading journals and scientists in physics.. Scientometrics, 2005, 64, 313-324.	1.6	5
169	Linear optical response of semiconductors. Journal of Electronic Materials, 1993, 22, 27-37.	1.0	4
170	Title is missing!. Journal of Low Temperature Physics, 1999, 117, 1049-1053.	0.6	4
171	Optical Properties I. Graduate Texts in Physics, 2005, , 243-343.	0.1	4
172	Optical Properties II. , 1999, , 333-413.		4
173	Resonant Raman scattering by plasmons in n-type Ge. Solid State Communications, 1984, 49, 1103-1105.	0.9	3
174	Alloy versus phonon contributions to intervalley scattering in Al <sub>1-x</sub> Ga <sub>x</sub> As. , 1992, 1677, 75.		3
175	Phonons, Electrons, and Electron-Phonon Interaction: Semiconductors and High-Tc Superconductors. , 2002, , 257-293.		3
176	Optical Properties II. Graduate Texts in Physics, 2005, , 345-426.	0.1	3
177	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions. , 1999, , 99-147.		3
178	Optical constants of pure and heavily doped silicon and germanium: Electronic interband transitions. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1983, 117-118, 356-358.	0.9	2
179	Light emission at the E1 and E1+ $\Gamma_1$ gaps in heavily doped p-type Ge and GaAs. Solid State Communications, 1985, 56, 549-552.	0.9	1
180	Electron and phonon self-energies in heavily doped germanium and silicon. Solid-State Electronics, 1985, 28, 31-38.	0.8	1

#	ARTICLE	IF	CITATIONS
181	On the value of author indices. Physics Today, 2011, 64, 9-10.	0.3	1
182	Optical Properties II. , 1996, , 333-413.		1
183	Faraday rotation in semiconductors. , 1962, , 72-88.		0
184	Photoelectron Spectroscopy. Graduate Texts in Physics, 2005, , 427-468.	0.1	0
185	Effect of Quantum Confinement on Electrons and Phonons in Semiconductors. Graduate Texts in Physics, 2005, , 469-551.	0.1	0
186	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions. Graduate Texts in Physics, 2005, , 107-158.	0.1	0
187	Electronic Band Structures. Graduate Texts in Physics, 2005, , 17-105.	0.1	0
188	Dielectric constant and long-wavelength refractive index vs. pressure and temperature in semiconductors. High Pressure Research, 2009, 29, 469-475.	0.4	0
189	Problems in Optical Properties of Semiconductors and their Solutions. , 1993, , 435-473.		0
190	Electronic Band Structures. , 1996, , 13-98.		0
191	Photoelectron Spectroscopy. , 1996, , 415-455.		0
192	Vibrational Properties of Semiconductors, and Electron-Phonon Interactions. , 1996, , 99-147.		0
193	Raman Scattering in Semiconductors with Reduced Translational Invariance. Kluwer International Series in Engineering and Computer Science, 1996, , 141-163.	0.2	0
194	Photoelectron Spectroscopy. , 1999, , 415-455.		0
195	Effect of Quantum Confinement on Electrons and Phonons in Semiconductors. , 1999, , 457-535.		0
196	Electronic Band Structures. , 1999, , 13-98.		0